IN THE SPECIFICATION:

Please replace paragraph [0029] with the following:

[0029] **Figure 2** presents a cross-sectional, schematic diagram of a deposition chamber **200** for comparison. The deposition chamber is a CVD chamber for depositing a carbon-based gaseous substance, such as a carbon-doped silicon oxide sublayer. This figure is based upon features of the ~~Producer S~~® PRODUCER® S APF™ chamber currently manufactured by Applied Materials, Inc. The PRODUCER® ~~Producer~~® CVD chamber (200 mm or 300 mm) has two isolated processing regions that may be used to deposit carbon-doped silicon oxides and other materials. A chamber having two isolated processing regions is described in United States Patent No. 5,855,681, which is incorporated by reference herein.

Please replace paragraph [0030] with the following:

[0030] The chamber **200** has a body **202** that defines an inner chamber area. Separate processing regions **218** and **220** are provided. Each processing region ~~chamber~~ **218**, **220** has a pedestal **228** for supporting a substrate (not seen) within the chamber **200**. The pedestal **228** typically includes a heating element (not shown). Preferably, the pedestal **228** is movably disposed in each processing region **218**, **220** by a stem **226** which extends through the bottom of the chamber body **202** where it is connected to a drive system **203**. Internally movable lift pins (not shown) are preferably provided in the pedestal **228** to engage a lower surface of the substrate. Preferably, a support ring (not shown) is also provided above the pedestal **228**. The support ring may be part of a multi-component substrate support assembly that includes a cover ring and a capture ring. The lift pins act on the ring to receive a substrate before processing, or to lift the substrate after deposition for transfer to the next station.

Please replace paragraph [0041] with the following:

[0041] **Figure 7** provides an exploded view of a chamber body portion **400**. In this instance, the chamber body **400** represents a tandem processing chamber. An example is the ~~Producer~~ PRODUCER® S chamber manufactured by Applied Materials, Inc. Various parts of a process kit **40** are seen arising from the processing region **404** on the right side of the body **402**.

Please replace paragraph [0045] with the following:

[0045] Below the blocker plate **480** is a shower head **490**. The shower head **490** is concentrically placed below the top cover **470**. The shower head **490** includes a plurality of nozzles (not seen) for directing gases downward onto the substrate (not seen). A face plate **496** and isolator ring **498** are secured to the shower head **490**. The isolator ring **498** electrically isolates the shower head **490** from the chamber body **402**. The isolator ring **498** is preferably fabricated from a smooth and relatively heat resistant material, such as ~~Teflon~~ TEFLON™ (*i.e.*, polytetrafluoroethylene) or ceramic.

Please replace paragraph [0054] with the following:

[0054] To further limit parasitic pumping at the area of the pumping port liners **442**, **444**, a seal member **427** is provided at the interface between the circumferential channel liner **420** and the upper pumping port liner **442**, and at the interface between the top liner **410** and the upper pumping port liner **442**. The seal member is visible at **427** in both **Figure 7** and **Figure 6B**. Preferably, the seal member **427** defines a circular ring that encompasses the upper pumping port liner **442**. The seal member **427** is preferably fabricated from a ~~Teflon~~ TEFLON™ (*i.e.*, polytetrafluoroethylene) material or otherwise includes a highly polished surface. The seal **427** further enables the circumferential channel liner **420** to interlock with the pumping port liners **442**, **444** and to limit gas leakage.

Please replace paragraph [0060] with the following:

[0060] It is also noted at this point that the filler member **430**, the pressure equalization port liner **436**, and the upper **442** and lower **444** pumping port liners are preferably coated with a highly smoothed material. An example is a shiny aluminum coating. Other materials provided with a very smooth surface, e.g., less than 15 Ra (roughness average) help reduce deposition accumulating on the surfaces. Such smooth materials may be polished aluminum, polymer coating, ~~Teflon~~ TEFLON™ (*i.e.*, polytetrafluoroethylene), ceramics and quartz.

Please replace paragraph [0064] with the following:

[0064] It is understood that the AFP™ chamber **400** of **Figure 7** is illustrative, and that the improvements of the present invention are viable in any deposition chamber capable of performing PECVD. Thus, other embodiments of the inventions may be provided. For example, the pumping liner **410** may have an inner diameter that is smaller than the inner diameter of the circumferential channel liner **420**. This reduced dimension for the top pumping liner **410** serves to reduce the inner diameter of the pumping port **405**, thereby increasing velocity of gases moving out of the processing region **404** and through the pumping port **405**. Increased gas velocity is desirable, as it reduces opportunities for carbon containing residue buildup on chamber surfaces. It is also desirable that the liners be fabricated from a material having a highly smooth surface. This serves to reduce amorphous carbon deposition from accumulating on the surface. Examples of such material again include polished aluminum, polymer coating, ~~Teflon~~ TEFLON™ (*i.e.*, polytetrafluoroethylene), ceramics, and quartz.